## NSN 5961-01-470-6985

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Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-470-6985 **Inclosure Material:** Ceramic **Overall Length:** 0.770 inches **Overall Height:** 0.175 inches **Overall Width:** 0.310 inches **End Application:** E/i fscm aircraft, b-2 bomber (atb) **Component Name And Quantity:** 4 transistor **Mounting Method: Terminal Semiconductor Material:** Silicon all transistor **Voltage Rating In Volts Per Characteristic:** 100.0 drain to source voltage all transistor and 100.0 drain to gate voltage all transistor and 20.0 gate to source voltage all transistor **Current Rating Per Characteristic:** 0.95 amperes source cutoff current of standard range all transistor **Power Rating Per Characteristic:** 1.4 watts small-signal input power, common-collector absolute all transistor **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius junction **Special Features:** Hardness critical process **Nuclear Hardness Critical Feature:** Hardened **Test Data Document:** 07690-632049 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 14 pin Shelf Life: N/a **Unit Of Measure: Demilitarization:**